

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)		Application Number	10596726
		Filing Date	2004-12-24
		First Named Inventor	YANSON et al.
		Art Unit	2828
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	305832-00130

U.S. PATENTS						
Examiner Initial*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines where Relevant Passages or Relevant Figures Appear
	1	6027989	A	2000-02-22	Poole et al.	
	2	6514784	B1	2003-02-04	Dubowski	

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	1	01/67497	WO	A1	2001-09-13	OOI et al.	

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Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, pages(s), volume-issue number(s), publisher, city and/or country where published.	T5
	1	TAEK, Y. et al., "Effect of dielectric -semiconductor capping layer combination on the dielectric cap quantum well disordering of InGaAs/InGaAsP quantum well structure", Technical Digest CLEO / Pacific Rim '99, Pacific Rim Conference on Lasers and Electro Optics Cat. No. 99TH8464, Vol. 3, p. 3 (1999)	<input type="checkbox"/>
	2	LIM, H. et al., "A novel fabrication technique for multiple-wavelength photonic-integrated devices in InGaAs-InGaAsP laser heterostructures", IEEE Photonics Technology Letters, 14:594-6 (May 2002)	<input type="checkbox"/>
	3	LIU, X. et al., "Control of multiple bandgap shifts in InGaAs-AlInGaAs multiple-quantum-well material using different thicknesses of PECVD SiO/sub 2/ protection layers", IEEE Photonics Technology Letters 12:1141-2 (2000)	<input type="checkbox"/>
	4	OOI, B., et al., "Selective Quantum-Well intermixing in GaAs-AlGaAs Structures Using Impurity-Free Vacancy Diffusion", IEEE J. Q. Elect. 33:1784-1793 (1997)	<input type="checkbox"/>
	5	AIMEZ, V. et al., "High precision metal masking for multiple wavelength laser diode fabrication using single step ion implantation induced quantum well intermixing," Proc. of the SPIE The International Society for Optical Engineering 4087:607-15 (2000)	<input type="checkbox"/>
	6	COLDREN, L., "ECE Technical Report 03-02: 2002 Reprints of Professor Larry A. Coldren and Collaborators", Dept. of Electrical and Computer Engineering, University of California, Santa Barbara (2002)	<input type="checkbox"/>
	7	MOERMAN, I. et al., "A Review on Fabrication Technologies for the Monolithic Integration of Tapers with III-V Semiconductor Devices", IEEE Journal of Selected Topics In Quantum Electronics, 3:1308-1320 (December 1997)	<input type="checkbox"/>
	8	BROEKAERT, T. P. E. et al., "AlAs Etch-Stop Layers for InGaAlAs/InP Heterostructure Devices and Circuits", IEEE Transactions on Electron Devices, 39:533-536 (March 1992)	<input type="checkbox"/>
	9	KOCH, T. L. et al., "Tapered Waveguide InGaAs/InGaAsP Multiple-Quantum-Well Lasers", IEEE Photonics Technology Letters, 2:88-90 (February 1990)	<input type="checkbox"/>
	10	UNITED KINGDOM PATENT OFFICE, Search Report in UK Patent Application Number GB0329915.3, June 24, 2004	<input type="checkbox"/>

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11	EUROPEAN PATENT OFFICE acting as the ISA/EP, International Search Report for PCT/GB2004/004944, March 11, 2005	<input type="checkbox"/>
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Examiner Signature	/Vicki Booker/	Date Considered	07/22/2009
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